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February 2007

# FDS6294

# 30V N-Channel Fast Switching PowerTrench® MOSFET

### **General Description**

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low  $R_{\text{DS(ON)}}$  and fast switching speed.

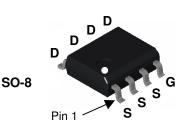
## **Applications**

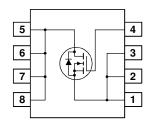
- DC/DC converter
- Power management
- · Load switch



### **Features**

- 13 A, 30 V.  $R_{DS(ON)} = 11.3 \ m\Omega \ @ \ V_{GS} = 10 \ V$   $R_{DS(ON)} = 14.4 \ m\Omega \ @ \ V_{GS} = 4.5 \ V$
- Low gate charge (10 nC typical)
- $\bullet$  High performance trench technology for extremely low  $R_{\text{DS}(\text{ON})}$
- High power and current handling capability.
- RoHS Compliant





# Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		30	V
V <sub>GSS</sub>	Gate-Source Voltage		± 20	V
I <sub>D</sub>	Drain Current - Continuous	(Note 1a)	13	Α
	- Pulsed		50	
P <sub>D</sub>	Power Dissipation for Single Operation	(Note 1a)	3.0	W
		(Note 1b)	1.2	
E <sub>AS</sub>	Single Pulse Avalanche Energy	(Note 3)	181	mJ
$T_J$ , $T_{STG}$	Operating and Storage Junction Temperature Range		-55 to +175	°C

### **Thermal Characteristics**

R <sub>eJA</sub>	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	(Note 1b)	125	
R <sub>eJC</sub>	Thermal Resistance, Junction-to-Case	(Note 1)	25	

**Package Marking and Ordering Information** 

Device Marking	Device	Reel Size	Tape width	Quantity
FDS6294	FDS6294	13"	12mm	2500 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \qquad I_{D} = 250  \mu\text{A}$	30			V
ΔBV <sub>DSS</sub> ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C		27		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, \qquad V_{GS} = 0 \text{ V}$			1	μА
I <sub>GSS</sub>	Gate-Body Leakage	$V_{GS} = \pm 20 \text{ V},  V_{DS} = 0 \text{ V}$			±100	nA
On Char	acteristics (Note 2)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	1	1.8	3	V
$\Delta V_{GS(th)} \ \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to 25°C		<b>-</b> 5		mV/°C
R <sub>DS(on)</sub>	Static Drain–Source On–Resistance	$\begin{split} &V_{GS} = 10 \text{ V}, & I_D = 13 \text{ A} \\ &V_{GS} = 4.5 \text{ V}, & I_D = 12 \text{ A} \\ &V_{GS} = 10 \text{ V}, I_D = 13 \text{ A}, T_J = 125 ^{\circ}\text{C} \end{split}$		9.4 11.5 13.5	11.3 14.4 16.5	mΩ
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = 10 \text{ V}, \qquad V_{DS} = 5 \text{ V}$	50			Α
<b>g</b> FS	Forward Transconductance	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 13 A		48		S
Dynamic	Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 15 \text{ V}, \qquad V_{GS} = 0 \text{ V},$		1205		pF
Coss	Output Capacitance	f = 1.0 MHz		323		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			102		pF
$R_G$	Gate Resistance	$V_{GS} = 15 \text{ mV},  f = 1.0 \text{ MHz}$		0.9		Ω
Switchin	g Characteristics (Note 2)					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 15 \text{ V}, \qquad I_{D} = 1 \text{ A},$		9	18	ns
tr	Turn-On Rise Time	$V_{GS} = 10 \text{ V}, \qquad R_{GEN} = 6 \Omega$		4	8	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			24	48	ns
t <sub>f</sub>	Turn-Off Fall Time			6	12	ns
Qg	Total Gate Charge	$V_{DS} = 15 \text{ V}, \qquad I_D = 13 \text{ A},$		10	14	nC
Q <sub>gs</sub>	Gate-Source Charge	$V_{GS} = 5 \text{ V}$		3.5		nC
$Q_{gd}$	Gate-Drain Charge			3		nC
Drain-Sc	ource Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain-Source	<u> </u>			2.1	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, \qquad I_S = 2.1 \text{ A (Note 2)}$		0.74	1.2	٧
t <sub>rr</sub>	Diode Reverse Recovery Time	$I_F = 13 \text{ A}, d_{iF}/d_t = 100 \text{ A}/\mu\text{s}$		25		nS
Q <sub>rr</sub>	Diode Reverse Recovery Charge			14		nC

#### Notes

<sup>1.</sup>  $R_{\text{eJA}}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\text{eJC}}$  is guaranteed by design while  $R_{\text{eCA}}$  is determined by the user's board design.



a) 50 °C/W when mounted on a 1in² pad of 2 oz copper



- b) 125°C/W when mounted on a minimum pad.
- Scale 1:1 on letter size paper

2. Test: Pulse Width < 300μs, Duty Cycle < 2.0%
3. Starting TJ = 25°C, L = 3mH, I<sub>AS</sub> = 11A,V<sub>DD</sub> = 30V, V<sub>GS</sub> = 10V

# **Typical Characteristics**

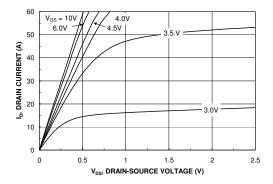


Figure 1. On-Region Characteristics.

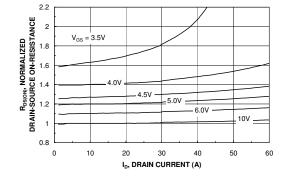


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

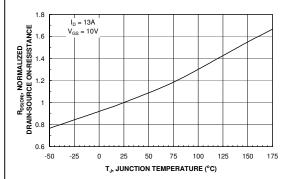


Figure 3. On-Resistance Variation with Temperature.

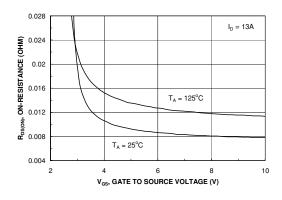


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

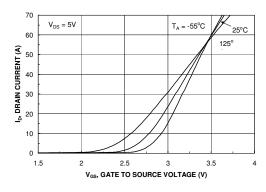


Figure 5. Transfer Characteristics.

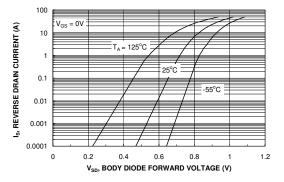
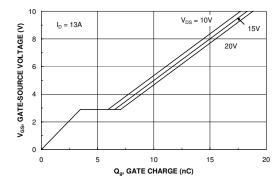


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

# **Typical Characteristics**



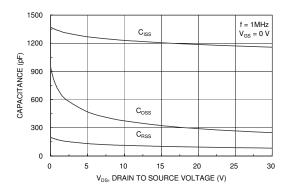
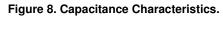
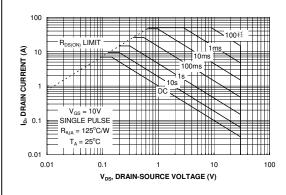


Figure 7. Gate Charge Characteristics.





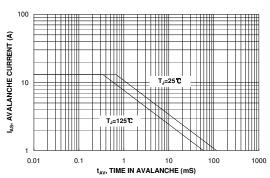
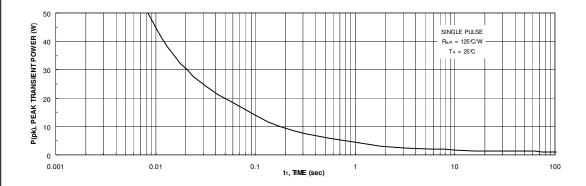


Figure 9. Maximum Safe Operating Area.

Figure 10. Unclamped Inductive Switching Capability Figure



11. Single Pulse Maximum Power Dissipation.



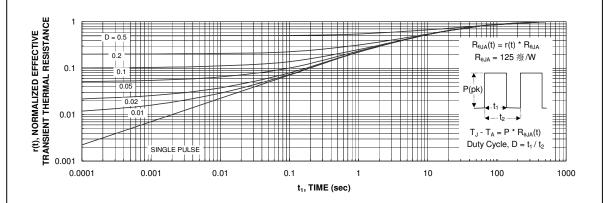


Figure 12. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

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